

**Silicon PNP Power Transistors**

**2SB794 2SB795**

**DESCRIPTION**

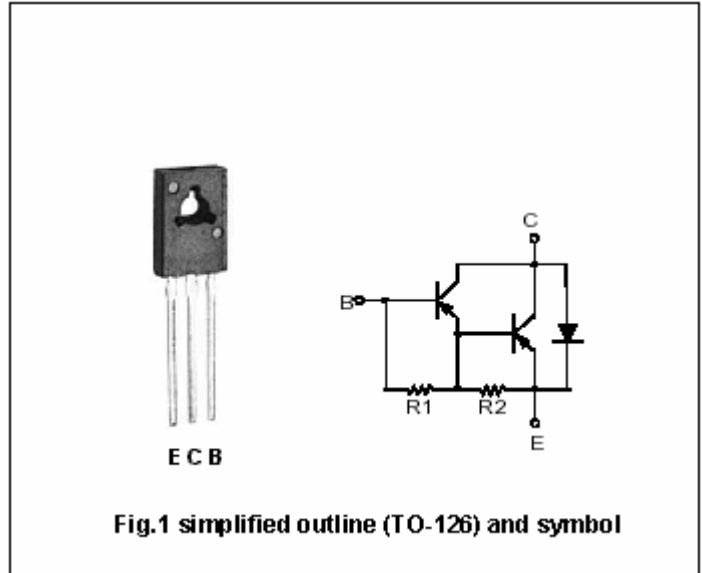
- With TO-126 package
- DARLINGTON
- High DC current gain
- Low collector saturation voltage
- Complement to type 2SD985 2SD986

**APPLICATIONS**

- For use in operating from IC without predriver ,such as hammer driver

**PINNING(See Fig.2)**

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base



**Absolute maximum ratings(Ta=25 )**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V <sub>CBO</sub>	Collector-base voltage	2SB794	-60	V
		2SB795	-80	
V <sub>CEO</sub>	Collector-emitter voltage	2SB794	-60	V
		2SB795	-80	
V <sub>EBO</sub>	Emitter-base voltage	Open collector	-8	V
I <sub>C</sub>	Collector current (DC)		-1.5	A
I <sub>CM</sub>	Collector current-peak		-3.0	A
P <sub>D</sub>	Total power dissipation	T <sub>a</sub> =25	1.0	W
		T <sub>C</sub> =25	10	
T <sub>j</sub>	Junction temperature		150	
T <sub>stg</sub>	Storage temperature		-55~150	

## Silicon PNP Power Transistors

## 2SB794 2SB795

## CHARACTERISTICS

T<sub>j</sub>=25 unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	2SB794	I <sub>C</sub> =-10mA ; I <sub>B</sub> =0	-60			V
		2SB795		-80			
V <sub>CEsat</sub>	Collector-emitter saturation voltage		I <sub>C</sub> =-1A ; I <sub>B</sub> =-1mA			-1.5	V
V <sub>BEsat</sub>	Base-emitter saturation voltage		I <sub>C</sub> =-1A ; I <sub>B</sub> =-1mA			-2.0	V
I <sub>CBO</sub>	Collector cut-off current	2SB794	V <sub>CB</sub> =-60V ; I <sub>E</sub> =0			-1.0	μA
		2SB795	V <sub>CB</sub> =-80V ; I <sub>E</sub> =0				
I <sub>EBO</sub>	Emitter cut-off current		V <sub>EB</sub> =-5V ; I <sub>C</sub> =0			-2.0	mA
h <sub>FE-1</sub>	DC current gain		I <sub>C</sub> =-0.5A ; V <sub>CE</sub> =-2V	1000			
h <sub>FE-2</sub>	DC current gain		I <sub>C</sub> =-1A ; V <sub>CE</sub> =-2V	2000		30000	

## Switching times

t <sub>on</sub>	Turn-on time	I <sub>C</sub> =-1.0A ; I <sub>B1</sub> =-I <sub>B2</sub> =-1.0mA V <sub>CC</sub> =-50V ; R <sub>L</sub> =50		0.5		μs
t <sub>stg</sub>	Storage time			1.0		μs
t <sub>f</sub>	Fall time			1.0		μs

◆ h<sub>FE-2</sub> Classifications

M	L	K
2000-5000	4000-10000	8000-30000

Silicon PNP Power Transistors

2SB794 2SB795

PACKAGE OUTLINE

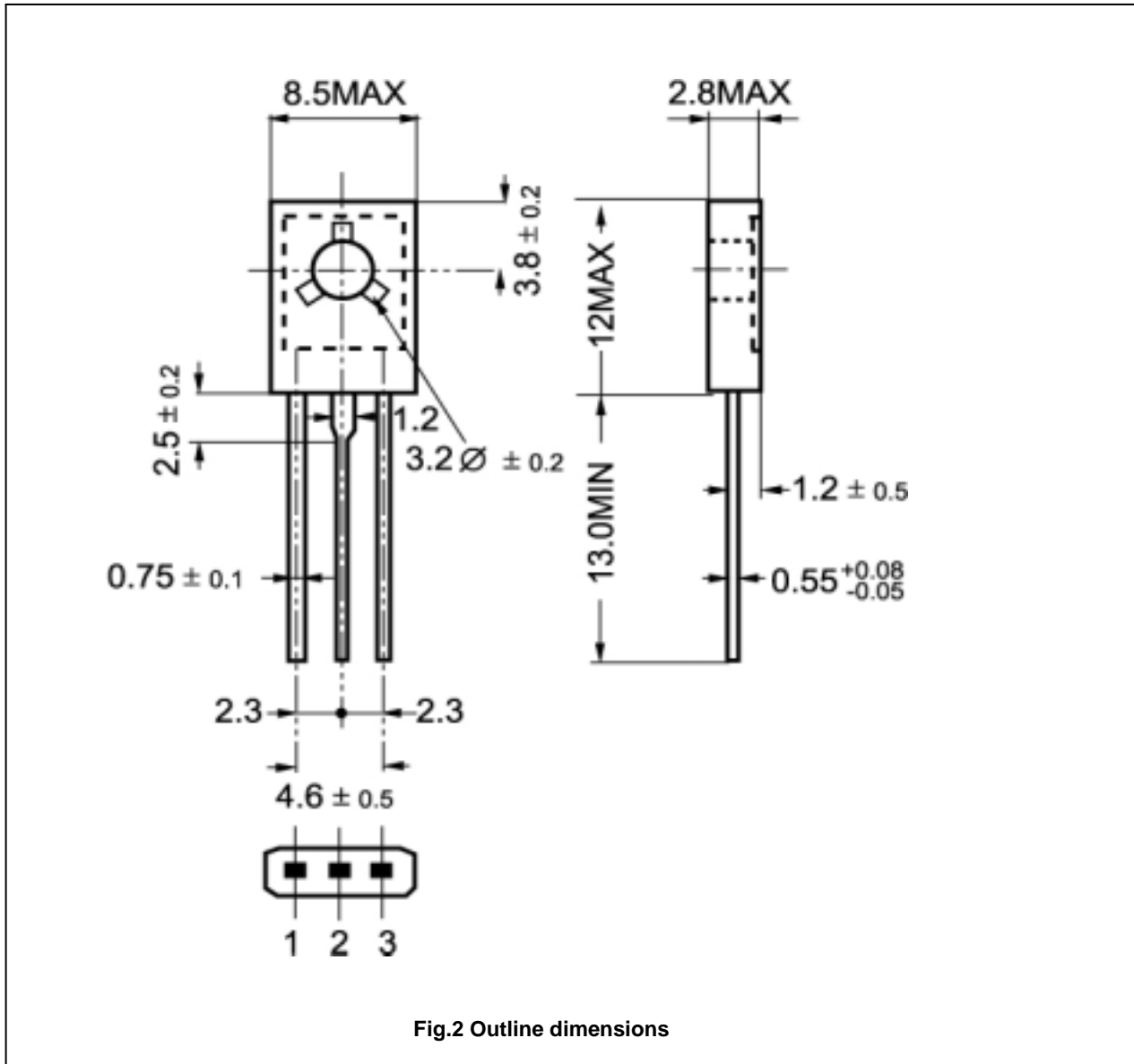


Fig.2 Outline dimensions